

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1 - 31 (cancelled)

Claim 32 (original) A method of forming a feature on a substrate that includes a first exposure with an alternating phase shift mask with full size scattering bars and a second exposure with a tritone attenuated mask having at least one scattering bar, said scattering bars are not printed in the resulting pattern from the lithography process.

Claim 33 (new) The method of claim **32** wherein said first exposure is comprised of patternwise exposing a positive tone photoresist layer on said substrate through said alternating phase shift mask with scattering bars using radiation comprised of one or more wavelengths from about 150 nm to 600 nm.

Claim 34 (new) The method of claim **32** further comprised of a single development step which follows the second exposure.

Claim 35 (new) The method of claim **33** wherein the resulting pattern is comprised of linewidths that are between $\frac{1}{4}$ and $\frac{1}{2}$ of the exposing wavelength in size.

Claim 36 (new) The method of claim **32** wherein said alternating phase shift mask is comprised of phase shift regions having a phase width that are separated by chrome regions.

Claim 37 (new) The method of claim **36** wherein said chrome regions are comprised of chrome lines that are used to define shrunken gates in said resulting pattern and full size scattering bars wherein from one to three scattering bars are positioned between each chrome line.

Claim 38 (new) The method of claim **37** wherein each chrome line and full size scattering bar separates a θ° phase shift region from a $(180 + \theta)^{\circ}$ phase shift region wherein θ is from 0 to 180.

Claim 39 (new) The method of claim **37** wherein said full size scattering bars have a width that is equal to or greater than the width of said chrome lines that define the shrunken gates.

Claim 40 (new) The method of claim **37** wherein said θ° phase shift region and said $(180 + \theta)^{\circ}$ phase shift region have phase widths that are equivalent.

Claim 41 (new) The method of claim **32** wherein the tritone attenuated mask is comprised of a transparent region, an attenuated phase shift region, and a chrome block region that protects a shrunken gate formed by said first exposure.

Claim 42 (new) The method of claim **41** wherein said attenuated phase shift region is comprised of an interconnect line feature having a width and a scattering bar which is a line parallel to said interconnect line feature and separated therefrom by a certain distance.

Claim 43 (new) The method of claim **42** wherein said scattering bar has a width that is 33% to 100% of the width of said interconnect line feature.

Claim 44 (new) The method of claim **42** wherein said certain distance between said scattering bar and said interconnect line feature is from about one to two times the width of said interconnect line feature.

Claim 45 (new) The method of claim **42** wherein said scattering bar is sub-resolution in width.